In the Specification:

Amend the paragraph that starts at page 4, line 14 (bridging to page 5) to read as follows:

Halo, or pocket, implants are well known as a means of moderating short-channel effects in very short MOSFETs. Short channel effects include Vt lowering and subthreshold slope increase as gate length decreases. Halo formation is usually accomplished by implanting a dopant type opposite to the source/drain doping, (e.g. by implanting boron in NFETs). A high energy is used for the halo implant to move it under the gate beyond the extent of the source/drain extension implant, which usually have significantly lower energies and higher doses, as shown in Table 1. As a result the p- dopant of the halo is often placed deeper than the n-dopant of the source/drain diffusion. The n-type source drain diffusion is thus decorated with a p-type halo all around. While the p-type dopant in the channel region is helpful for short channel effect, the halo extending under the source/drain has the unfortunate effect of increasing source/drain junction capacitance. Note that in the description below, the phrase "(#) e (#)" is a shorthand notation for concentrations in powers of ten; thus, e.g. in the table below, "1e13" means $1x10^{13}$.

In the Claims:

Cancel Claims 1-4, without prejudice.

5. (Amended) An FET comprising:

a gate having a top and bottom portion, the top portion having a width that is greater than the width of the bottom portion;

a first diffusion self-aligned to the bottom portion; and

a second implant defined by said top portion.

7. (Amended) The FET as recited in claim 7, further comprising a spacer adjacent said top portion and a third implant defined by said spacer.